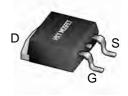


### **Description**

The IRFR3709ZTRPBF uses advanced trench technology

to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a

Battery protection or in other Switching application.



#### TO-252-2L

#### **General Features**

 $V_{DS} = 30V I_{D} = 80 A$ 

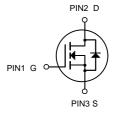
 $R_{DS(ON)} < 6.8 m\Omega$  @  $V_{GS} = 10 V$ 

## **Application**

**Battery protection** 

Load switch

Uninterruptible power supply



N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
IRFR3709ZTRPBF	TO-252-2L	RFR3709 XXXX	2500

## Absolute Maximum Ratings (T<sub>C</sub>=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
	Drain Current – Continuous (Tc=25°C)	80	А
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =100°C)	51	А
Ірм	Drain Current – Pulsed¹	320	А
EAS	Single Pulse Avalanche Energy <sup>2</sup>	88	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	42	А
_	Power Dissipation (T <sub>C</sub> =25°C)	54	W
P <sub>D</sub>	Power Dissipation – Derate above 25°C	0.43	W/°C
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θ</sub> JA	Thermal Resistance Junction to ambient	62	°C/W
Reлc	Thermal Resistance Junction to Case	2.3	°C/W

### N-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
△BVDSS/△TJ	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.04		V/°C
		V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			10	uA
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
DD 0 ( 0 \ 1)	Static Drain-Source On-Resistance <sup>3</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =20A		5	6.8	mΩ
RDS(ON)		V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A		6.5	9	mΩ
VGS(th)	Gate Threshold Voltage		1	1.6	2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$-V_{GS}=V_{DS}$ , $I_D=250uA$		-4		mV/°C
gfs	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =10A		18		S
$Q_g$	Total Gate Charge <sup>3, 4</sup>			11.1		
Qgs	Gate-Source Charge <sup>3, 4</sup>	$V_{DS}$ =15V , $V_{GS}$ =4.5V , $I_{D}$ =20A		1.85		nC
Qgd	Gate-Drain Charge <sup>3 , 4</sup>			6.8		
Td(on)	Turn-On Delay Time <sup>3, 4</sup>			7.5		
T <sub>r</sub>	Rise Time <sup>3, 4</sup>	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$		14.5		ns
Td(off)	Turn-Off Delay Time <sup>3,4</sup>	I <sub>D</sub> =15A		35.2		
$T_f$	Fall Time <sup>3,4</sup>			9.6		
Ciss	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , F=1MHz		1160		pF
Coss	Output Capacitance			200		
Crss	Reverse Transfer Capacitance			180		
$R_g$	Gate resistance	$V_{GS}$ =0V, $V_{DS}$ =0V, F=1MHz		2.5		Ω
EAS	Single Pulse Avalanche Energy	V <sub>DD</sub> =25V, L=0.1mH, IAS=20A	20			mJ
IS	Continuous Source Current				80	А
ISM	Pulsed Source Current <sup>3</sup>	¬V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			320	Α
VSD	Diode Forward Voltage <sup>3</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C		-	1	V
trr	Reverse Recovery Time	VGS=0V,IS=1A , di/dt=100A/μs T <sub>J</sub> =25°C		-		ns



### **Typical Characteristics**

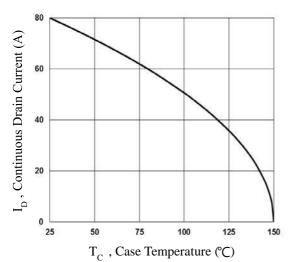


Fig.1 Continuous Drain Current vs. Tc

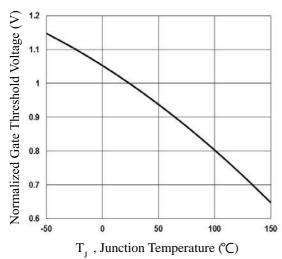


Fig. 3 Normalized Vth vs. Tj

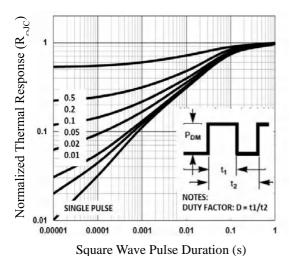


Fig.5 Normalized Transient Impedance

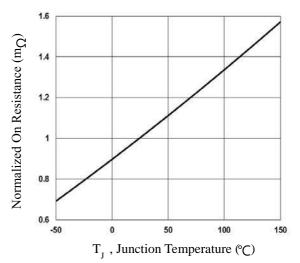


Fig.2 Normalized RDSON vs. Tj

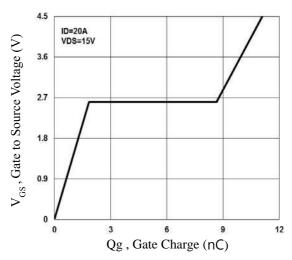


Fig. 4 Gate Charge Waveform

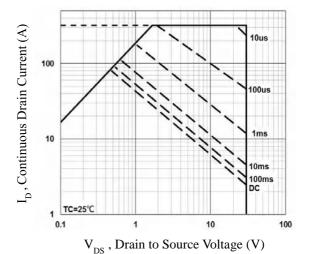
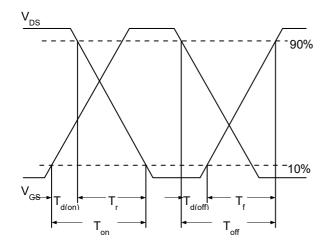


Fig.6 Maximum Safe Operation Area

# IRFR3709ZTRPBF

N-Channel Enhancement Mode MOSFET



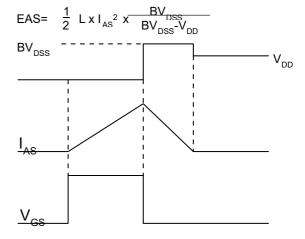
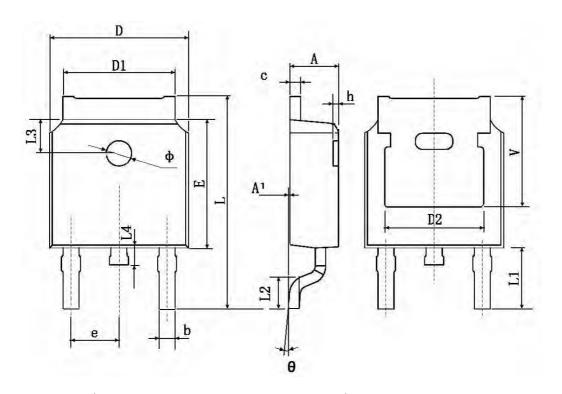


Fig. 7 Switching Time Waveform

Fig. 8 EAS Waveform

# **TO-252-2L Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		

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